



Sheet 1 of 1

Form PTO/SB/469 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 117087		APPLICATION NO. 10/663,902	
		INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT Satoshi TANENAKA			
				FILING DATE September 17, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS
SD	1	JP A 7-142735 (with abstract and translation)	06/02/1995	Japan			
SD	2	JP A 6-120249 (with abstract and translation)	04/28/1994	Japan			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
EXAMINER				DATE CONSIDERED 8-15-04			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: February 5, 2004

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. 117087		APPLICATION NO. New US Application	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT Satoshi TAKENAKA				
		FILING DATE September 17, 2003				
		U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)						
<i>SD</i>	I	Yazaki et al., "Conduction Mechanism of Leakage Current Observed in Metal-Oxide-Semiconductor Transistors and Poly-Si Thin-Film Transistors", Jpn. J. Appl. Phys., Vol. 31 (1992), pp 206-209 <i>JAN</i>				
EXAMINER <i>SD</i>		DATE CONSIDERED <i>8-15-04</i>				
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						